

# KKR & LDA

## Introduction

Consider following systems:  $M$  fixed nuclei  $(R_i, Z_i)$  and  $N$  electrons  $(r_i)$  in their ground state.

Schrodinger equation:

$$\left\{ -\frac{\hbar^2}{2m} \sum_j \nabla_j^2 + \sum_j v(r_j) + \frac{1}{2} \sum_{\substack{j, j' \neq 1 \\ j \neq j'}}^N \frac{e^2}{|r_j - r_{j'}|} - E \right\} \Psi(r_1, \dots, r_N) = 0, \quad (1)$$

PHYSICAL REVIEW

VOLUME 94, NUMBER 5

JUNE 1, 1954

### Solution of the Schrödinger Equation in Periodic Lattices with an Application to Metallic Lithium\*

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(Received December 23, 1953)

The problem of solving the Schrödinger equation in a periodic lattice is studied from the point of view of the variation-iteration method. This approach leads to a very compact scheme if the potential  $V(r)$  is spherically symmetrical within the inscribed spheres of the atomic polyhedra and constant in the space between them. The band structure of the lattice is then determined by (1) geometrical structure constants, characteristic of the type of lattice and (2) the logarithmic derivatives, at the surface of the inscribed sphere, of the  $s, p, d, \dots$  functions corresponding to  $V(r)$ . By far the greater part of the labor is involved in the calculation of (1), which needs to be done only once for each type of lattice; (2) can be obtained by numerical integration or directly from the atomic spectra. Although derived from a different point of view, this scheme turns out to be essentially equivalent to one proposed by Korringa on the basis of the theory of lattice interferences. The present paper also contains an application to the conduction band of metallic lithium.

&

$$\frac{e^2}{|r_j - R_i|} \quad (2)$$

ren  $(R_i, Z_i)$  what are distribution)?

methods for solving S.E. (1)

feasible for  $N \approx N_0$ ,

where typically  $N_0 \sim 10$  or so.

# Resolvents:

- $G(z) = (z - H)^{-1}$  resolvent: analytic in the complex plane with exception of the poles on the real axis; Green's functions: e.g.,  $\langle \mathbf{r} | G(z) | \mathbf{r}' \rangle$  are representations of  $G(z)$
- $H$  : non-relativistic or relativistic (Dirac)
- $G(z)$  and  $H$  have the same symmetry
- physical properties can be formulated as mappings of  $G(z)$

# Lippmann-Schwinger equation

$$G(z) = G_0(z)[1 + VG(z)]$$

$G_0(z)$ : structure constants,  $V = \text{const.}$ ,

„screened KKR“, semi-infinite systems

$G_0(z)$ : semi-infinite system,  $V = \text{set of „impurity“}$

potentials: „embedded cluster method“,

nanostructures

# Configurational averages

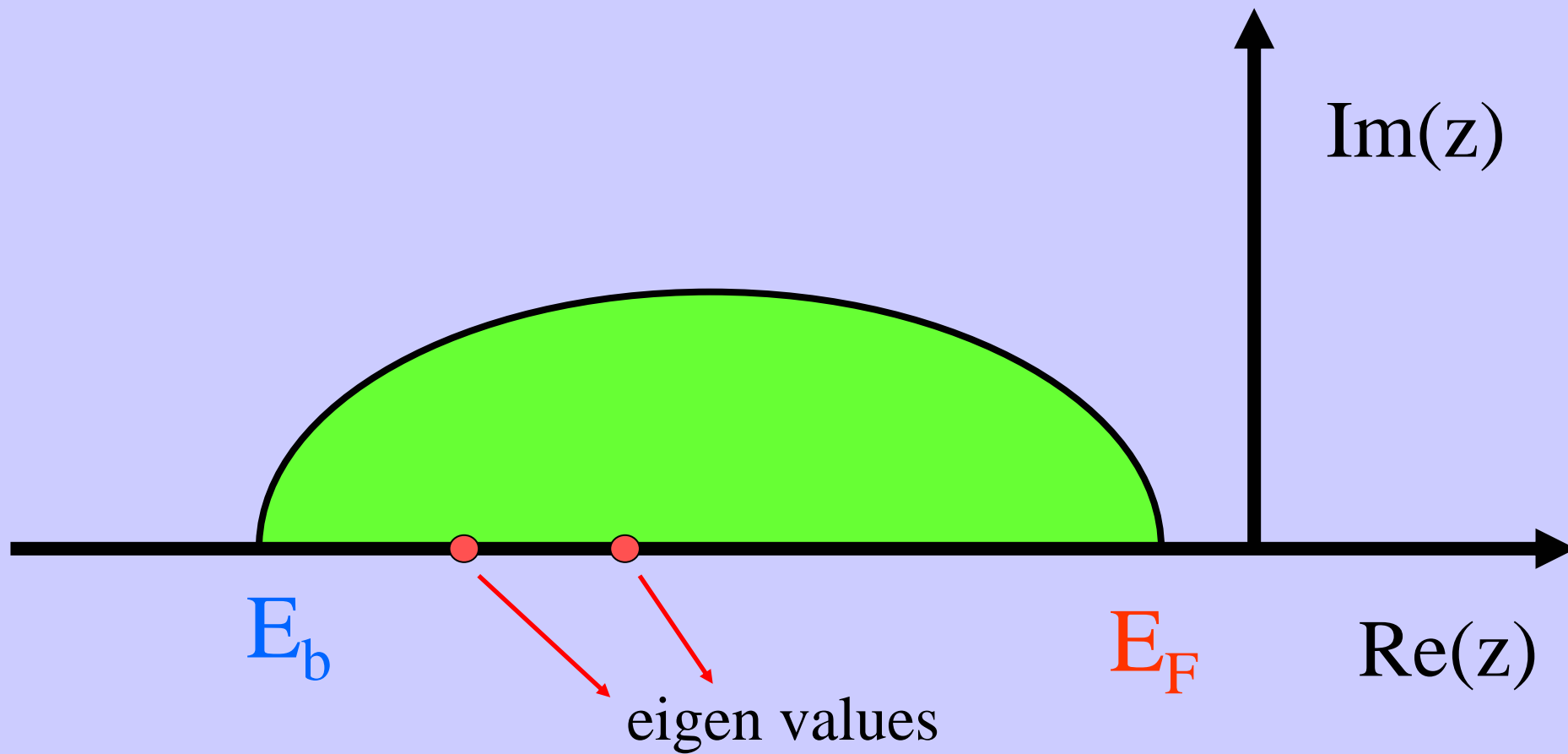
$$\langle G(z) \rangle_{\text{conf}} = c_A \langle G(z) \rangle_A + c_B \langle G(z) \rangle_B$$

$\langle G(z) \rangle_{A,B}$  : partial average

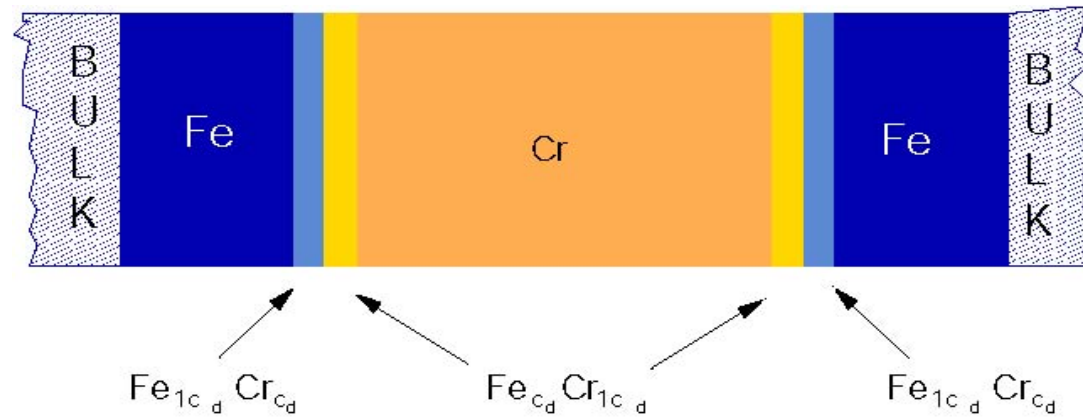
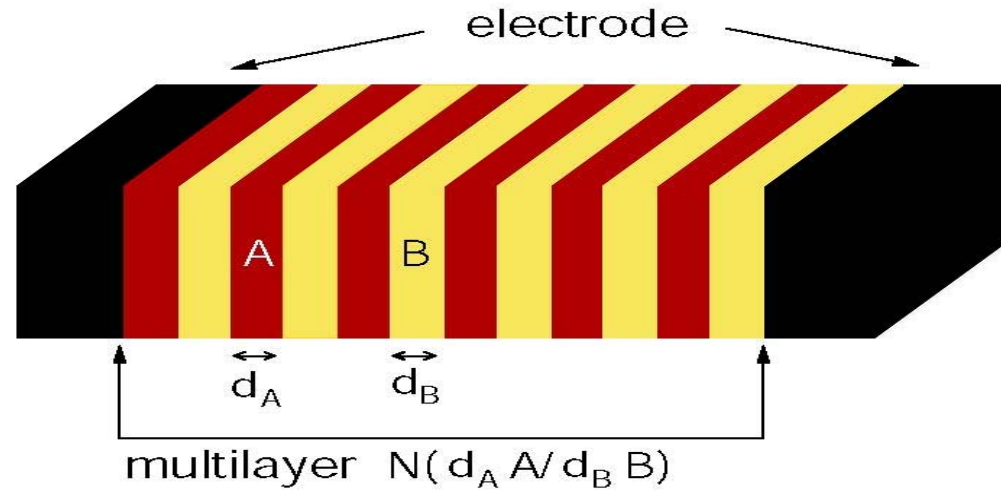
c: can be inhomogeneous (layered systems)

Coherent Potential Approximation (CPA)

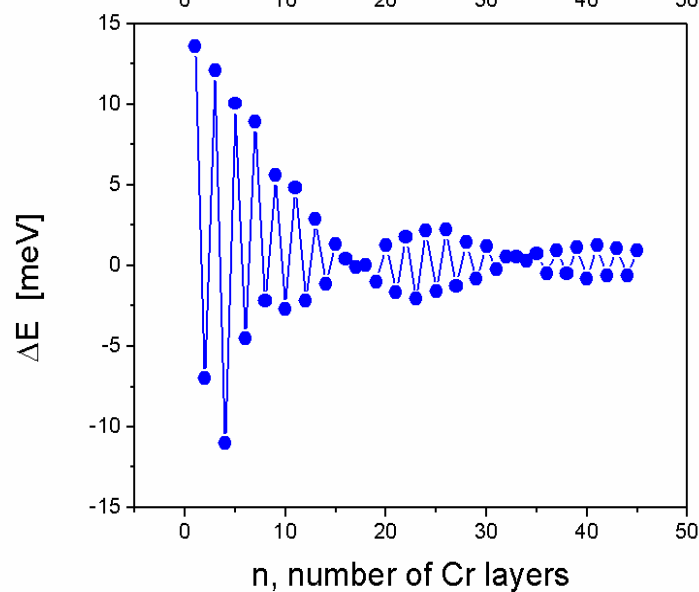
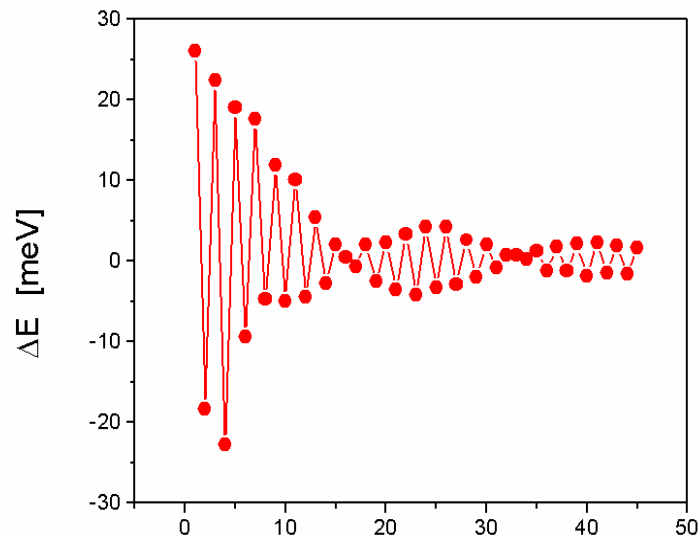
# Contour integrations



# Magnetic multilayers



bcc-Fe(100)|Cr<sub>n</sub>|Fe<sub>6</sub>|Vac



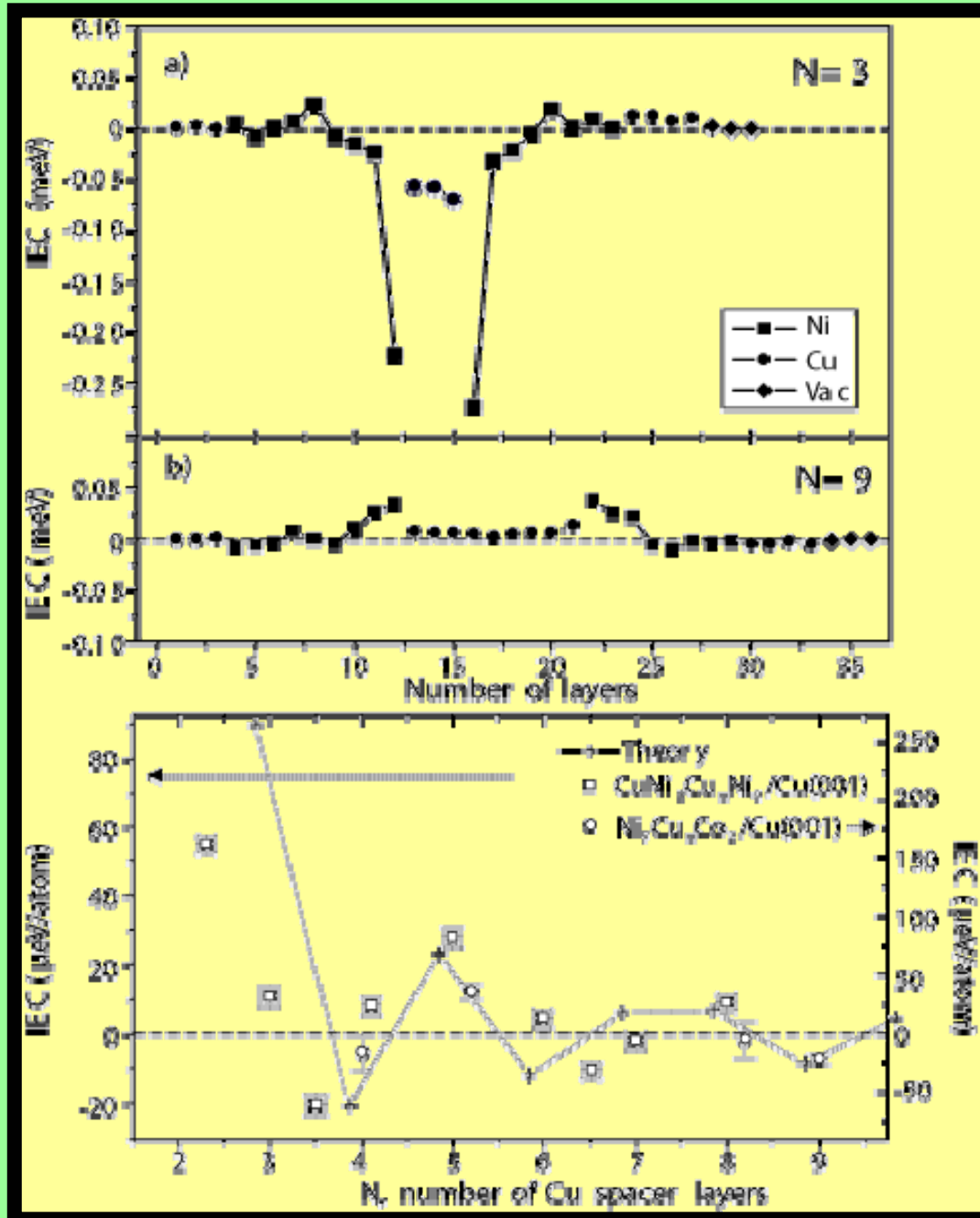
Interlayer  
exchange  
coupling (IEC)

$180^\circ$  coupling

$90^\circ$  coupling

- (1) Phase slip
- (2) Oscillatory, two periods

# IEC & experiment



$\text{Cu}_4\text{Ni}_8\text{Cu}_5\text{Ni}_9/\text{Cu}(100)$

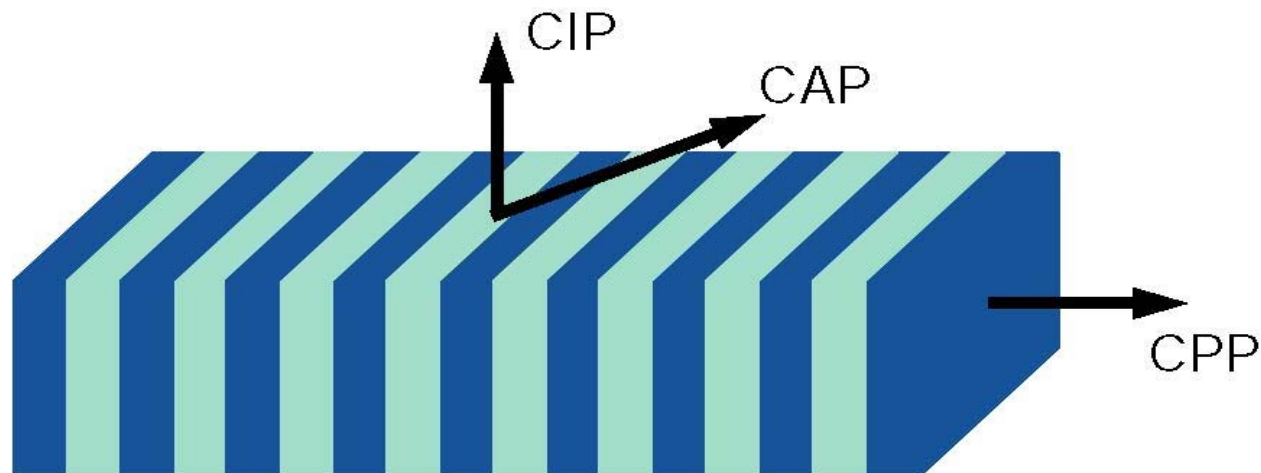
# Electric transport

CIP: „current-in-plane“

CPP: „current-perpendicular to the planes of atoms“

GMR: giant magnetoresistance

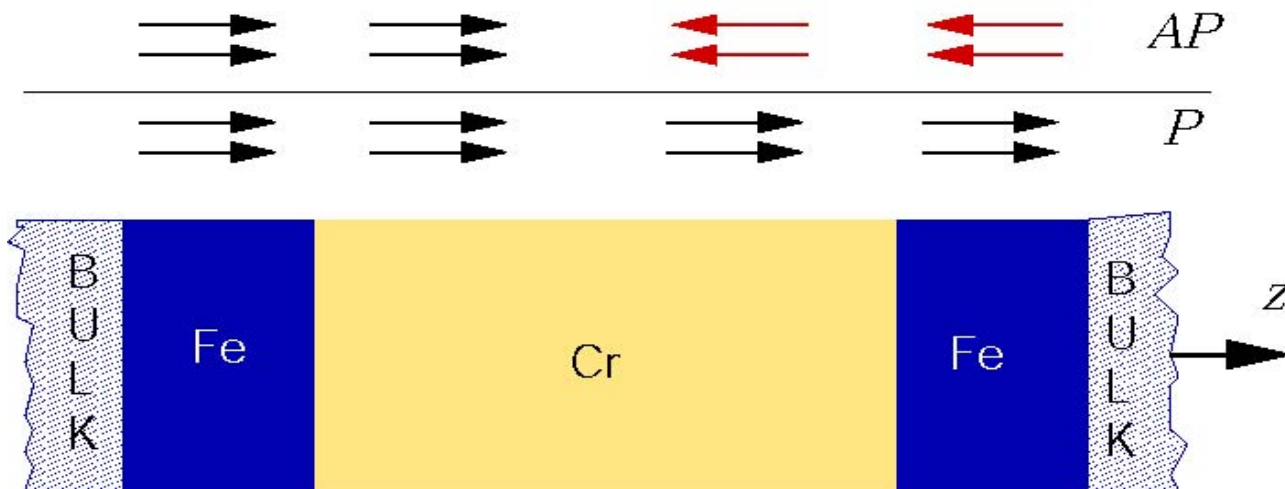
TMR: tunneling magnetoresistance



# Magnetic configurations

P: parallel („ferromagnetic“)

AP: antiparallel („antiferromagnetic“)



Suppose that in the Kubo-Greenwood equation the current operator can be approximated by a constant,

$$\bar{\sigma} \sim \text{tr} \langle \text{Im} G^+(\epsilon_F) \text{Im} G^+(\epsilon_F) \rangle \sim n^2(\epsilon_F) \quad , \quad (1)$$

which in turn implies that the sheet resistance can be written approximately as

$$\bar{r} = L\bar{\sigma}^{-1} = Ln^{-2}(\epsilon_F) \quad . \quad (2)$$

Furthermore, suppose the density of states is calculated for complex Fermi energies,  $\mathcal{E}_F = \epsilon_F + i\delta$ ,

$$\bar{r}(\delta) = L\bar{\sigma}^{-1} = Ln^{-2}(\epsilon_F + i\delta) \quad , \quad (3)$$

then from the properties of the density of states,

$$\frac{d[n(\epsilon_F + i\delta)]}{d\delta} = \begin{cases} > 0; \text{ "non-metallic" } \\ < 0; \text{ "metallic" } \end{cases} \quad , \quad (4)$$

follows immediately

# Physical meaning of complex Fermi energies I

$$\frac{d[\bar{r}(\delta)]}{d\delta} = \begin{cases} > 0; \text{ "metallic"} \\ < 0; \text{ "non-metallic"} \end{cases} \quad (5)$$

The functional form of the actually calculated sheet resistance with respect to the imaginary part of the Fermi energy can therefore be used to *qualitatively interpret* the underlying type of conduction

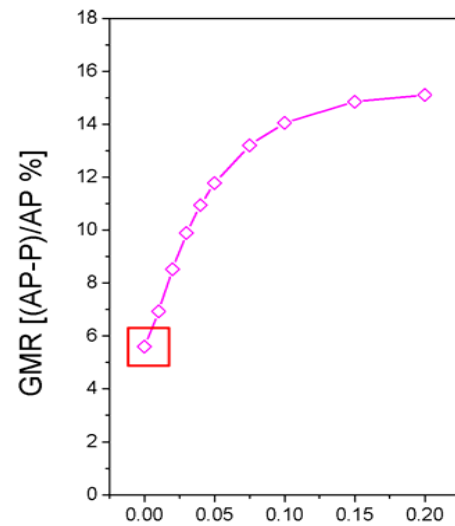
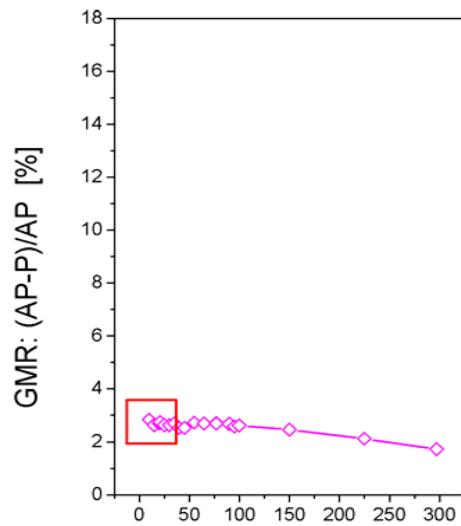
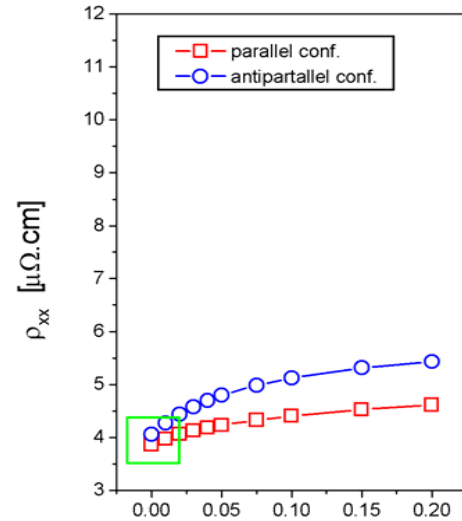
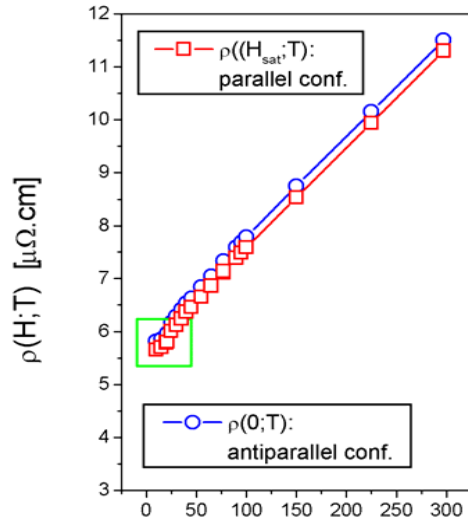
$$\frac{d[r(C; s; \delta)]}{d\delta} = \begin{cases} > 0; \text{ "metallic"} \\ < 0; \text{ "non-metallic"} \end{cases} \quad (6)$$

The last equation means *inter alia* that in the case of a negative slope of the sheet resistance with respect to  $\delta$  "tunneling" might occur.

**The parameter  $\delta$  obviously acts like a (small) constant selfenergy:** in the regime of metallic conduction an increase of the selfenergy implies an increased resistivity (sheet resistance); in the non-metallic regime an increase of  $\delta$  reduces the resistance, the system becomes more metallic.

## Physical meaning of complex Fermi energies II

## Fe/Au/Fe/Au Multilayer



**T [K]**  
Experiment

interdiffusion concentration  
Theory

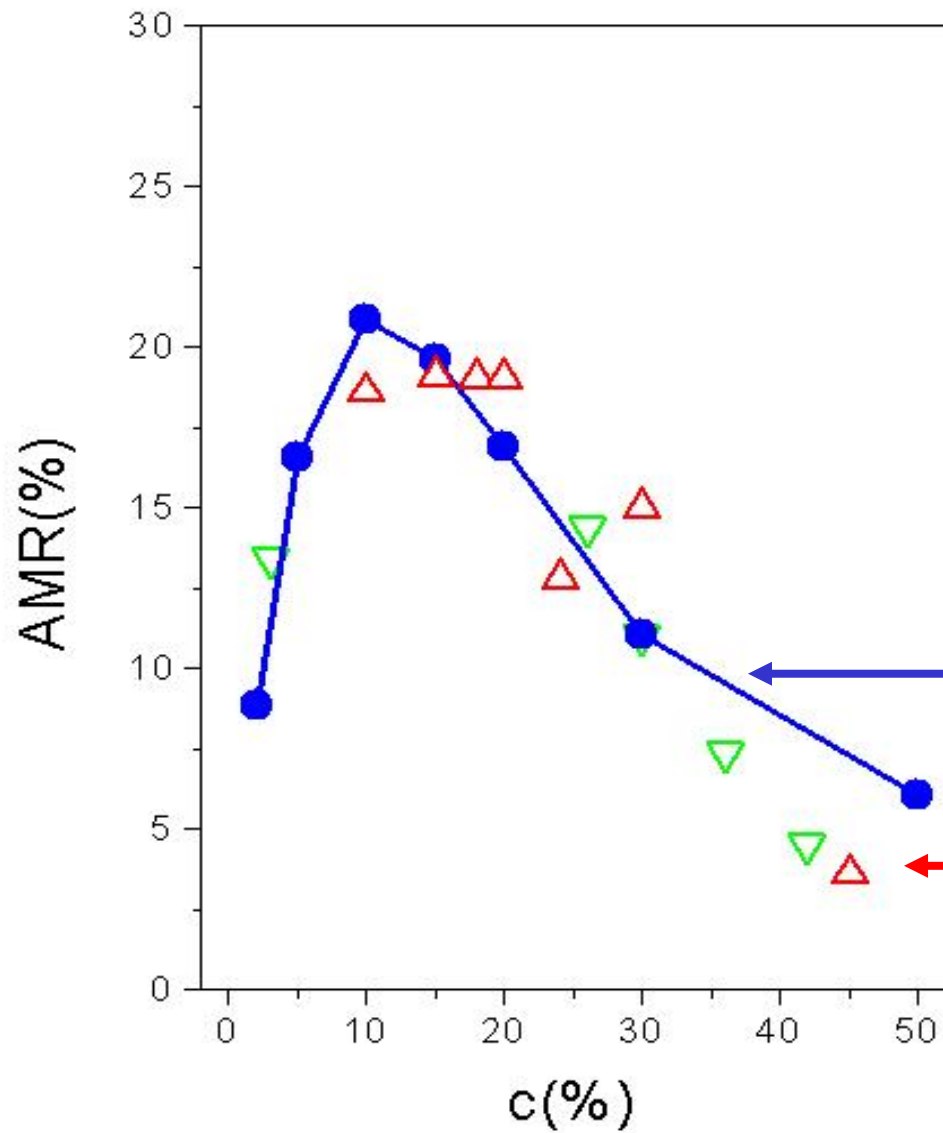
# Resistivities & GMR in magnetic multilayers

# AMR in Permalloy

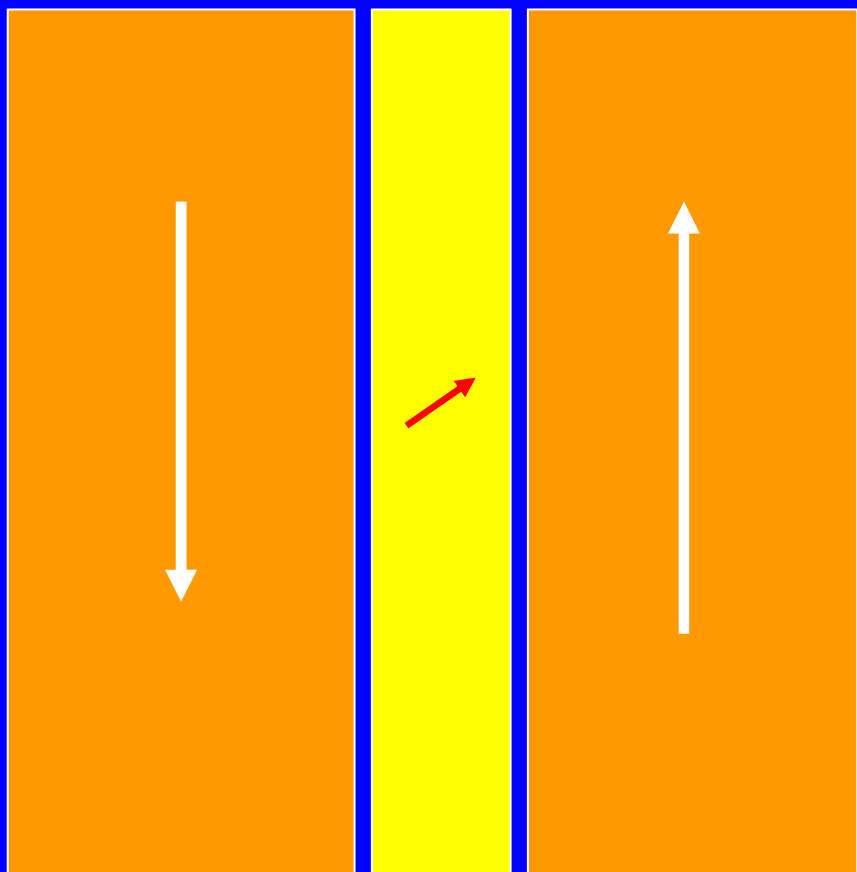


Theory

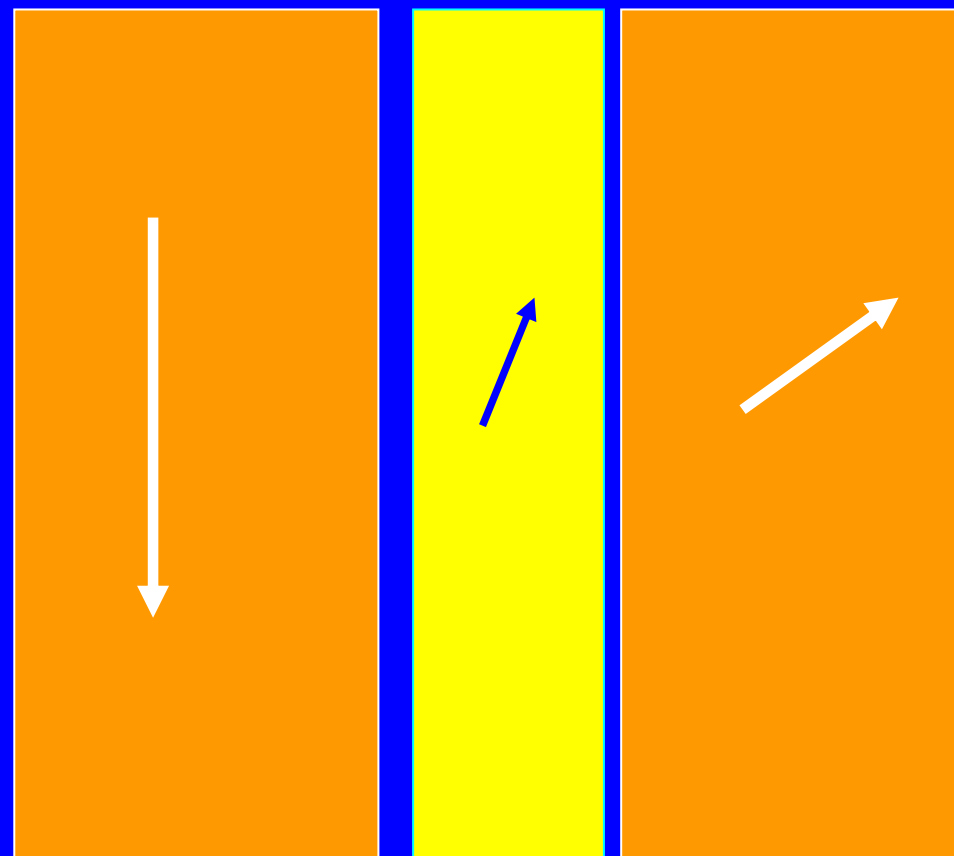
Experiment



# Magnetic domains



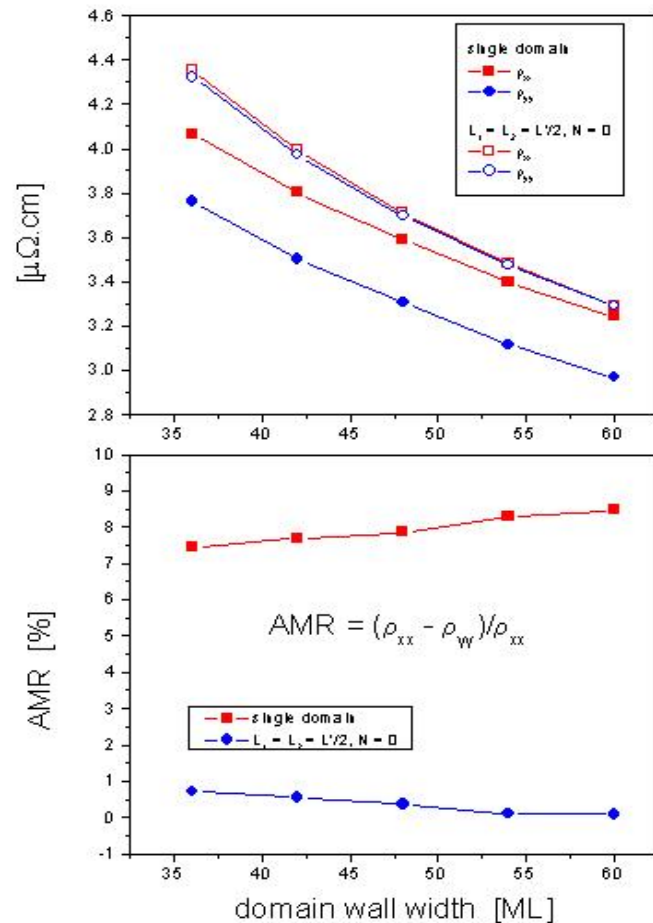
180° domains



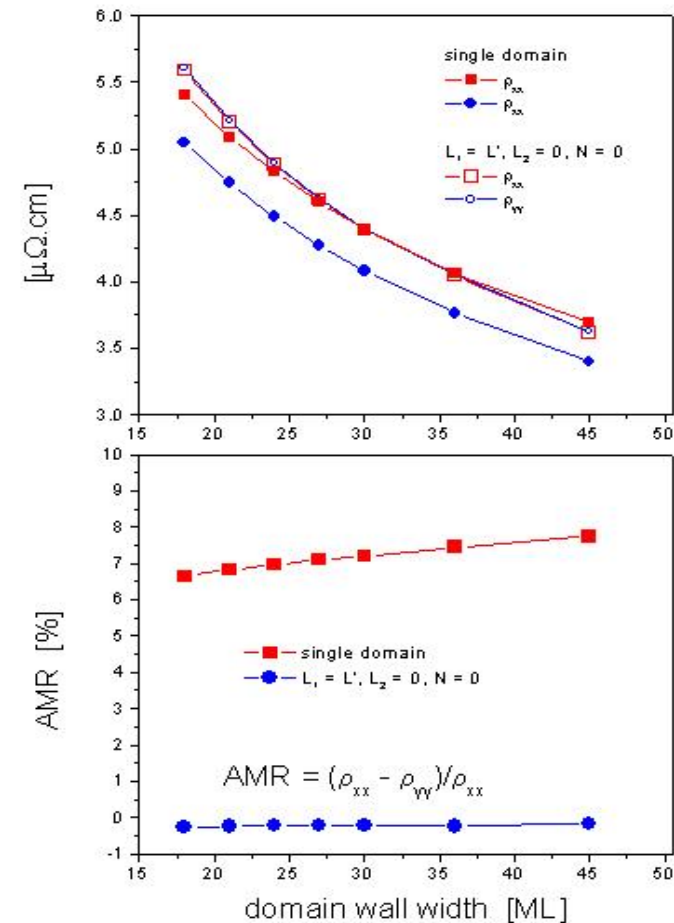
90° domains

# CIP-AMR in permalloy domain walls

## 180° domain wall



## 90° domain wall



# Exchange bias

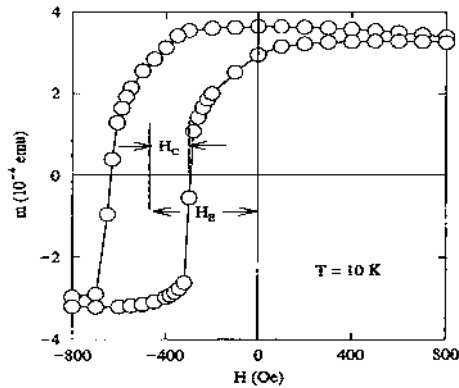


Fig. 1. Hysteresis loop,  $m(H)$ , of a  $\text{FeF}_2/\text{Fe}$  bilayer at  $T = 10 \text{ K}$  after field cooling [72]. The exchange bias,  $H_E$ , and the coercivity,  $H_C$ , are indicated in the figure.

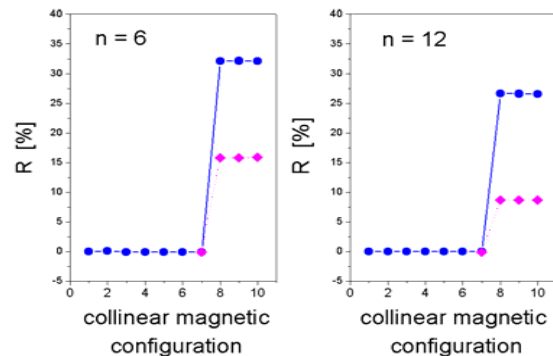
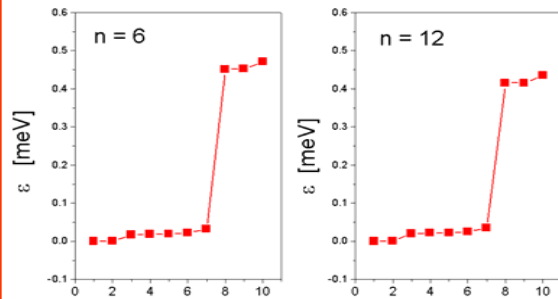
AFM/FM systems:  
Magnetic pinning

Exchange bias for  
GMR-devices:

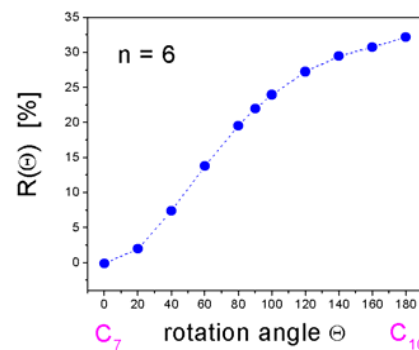
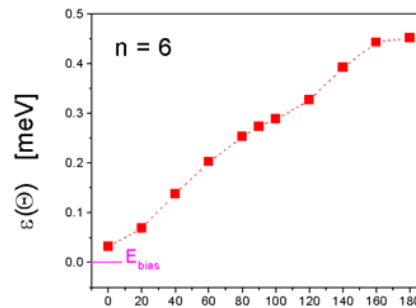
$$0 < E < E_{\text{bias}} : R(E) = 0$$

$$E > E_{\text{bias}} : R(E) > 0$$

$E$ : interlayer exchange energy



$\text{Co}(111)/\text{Co}_9/(\text{CoO})_n/\text{Co}_9/\text{Cu}_6/\text{Co}_9/\text{Co}(111)$

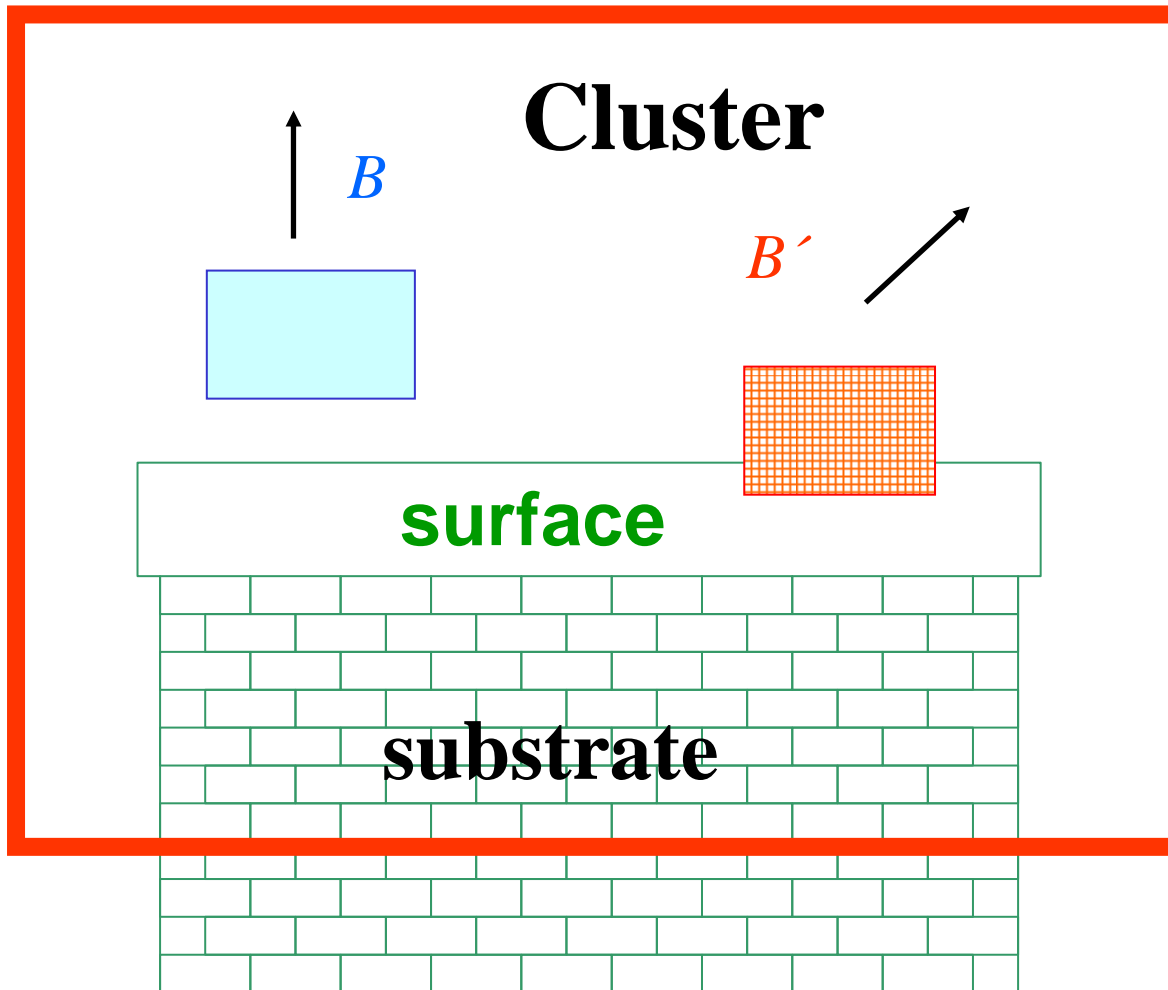


CoO/Co:

$$E_{\text{bias}}(\text{exp.}) < 9.5 \text{ kO}$$

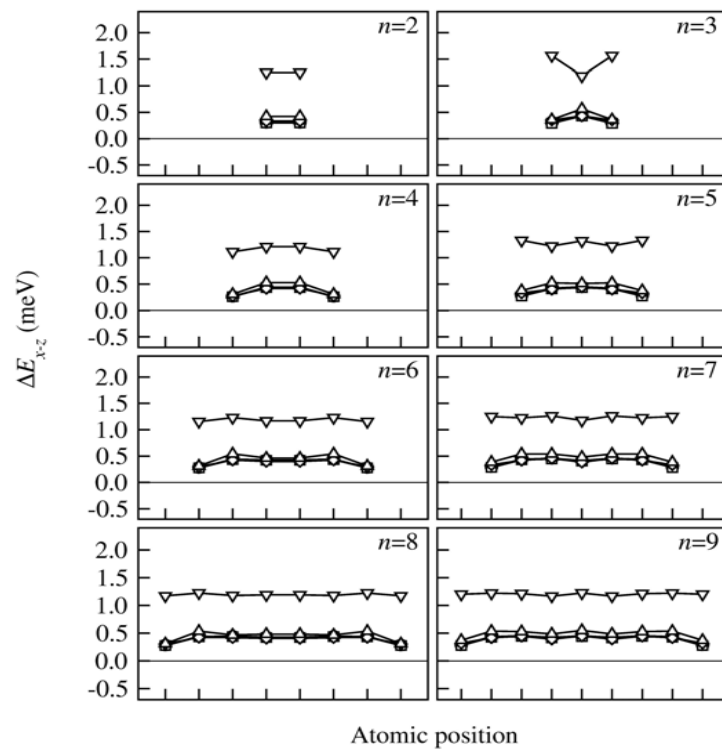
$$E_{\text{bias}}(\text{theor.}) = 6 \text{ kO}$$

# Nanostructures

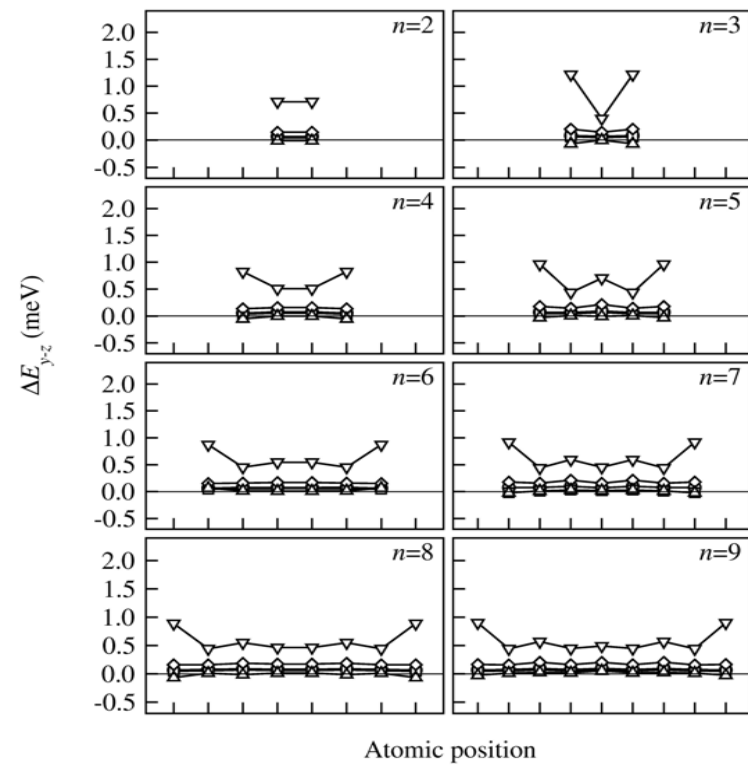


# Magnetic anisotropy of nanostructures

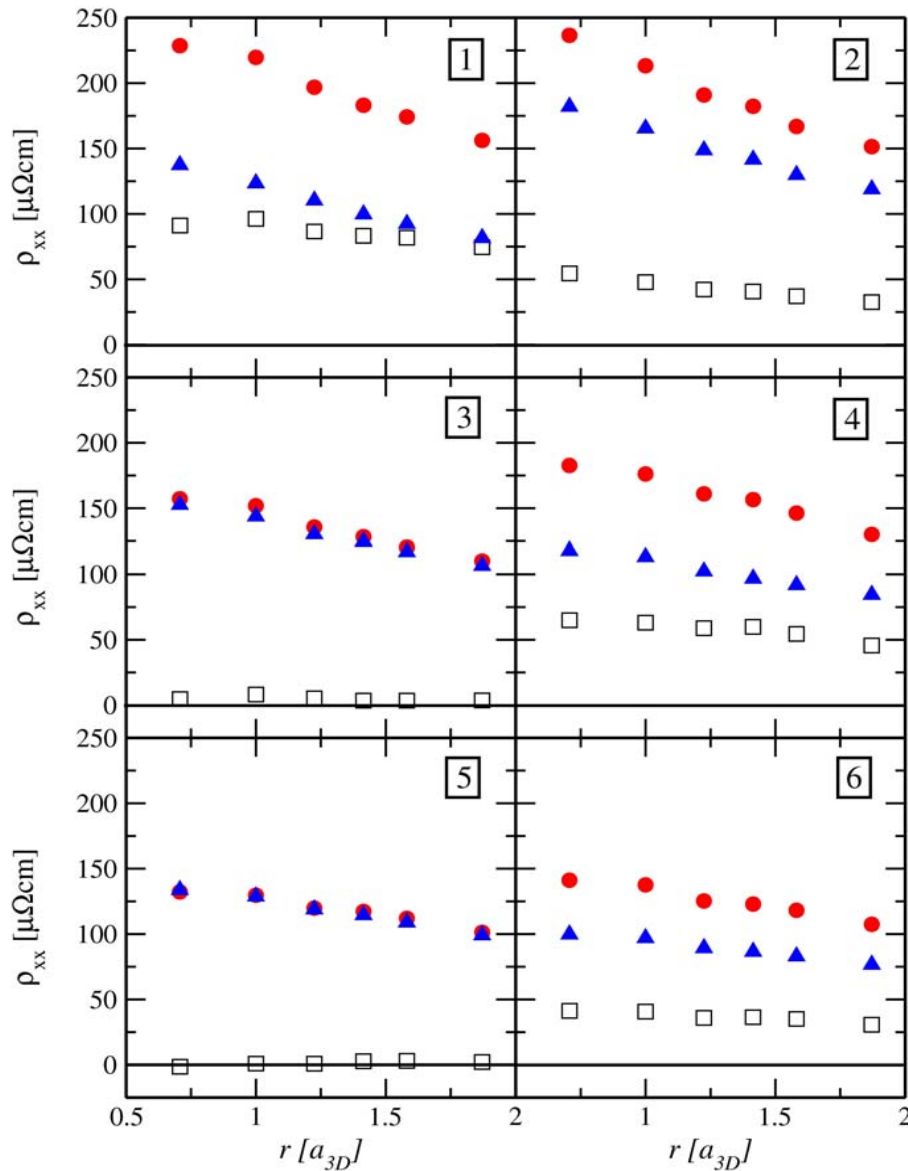
$\text{Fe}_n/\text{Cu}(100)$



$\text{Fe}_n/\text{Cu}(111)$



# Electric properties of nanostructures



Residual resistivities of finite chains of Fe (circles) and Co (triangles) atoms embedded in the surface plane of Ag(100). Open squares refer to the difference between the Fe and the Ni residual resistivity. The length of the chains is shown explicitly.

# Time-dependent DFT-1



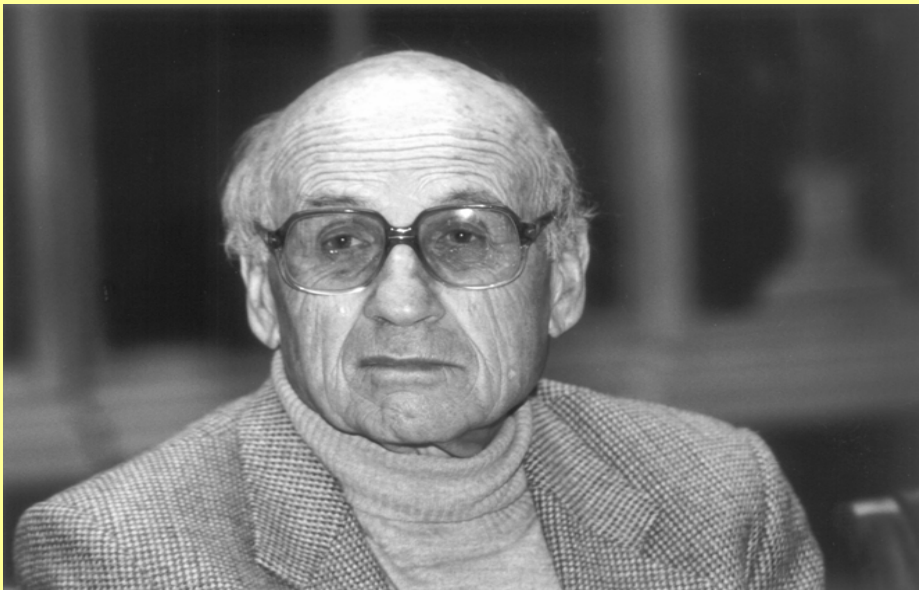
-74

-58

t, [a]

# Time-dependent DFT-2

The famous WK-guacamole



- 5

- 1/2

t, [a]